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2N332 - 2N336 thru 2N332A - 2N336A

NPN Silicon Diffused Transistors

APPLICATIONS

These transistors are general purpose silicon diffused transistors intended for amplifier applications in the audio and RF range and for general purpose switching applications. These units are highly stable and their variation in gain with current and temperature is less than with grown junction types.

MAXIMUM RATINGS

Maximum Dissipation - Free Air
Maximum Operating and/or Storage Temperature

500mW -65 to 200°C

DESIGN CHARACTERISTICS AT 25°C (Except as Noted)

| ١ | | | 2N332 | 2N332A | 2N333 | 2N333A | 2N334 | 2N334A | 2N335 | 2N335A | 2N336 | 2N336A | |
|-----|----------------------|--|-----------|-----------|-----------|-----------|-----------|-----------|-----------|-----------|-----------|-----------|-------------|
| | SYMBOL | TEST CONDITIONS | Min. Max. | UNIT |
| | BV _{CBO} | $I_{C} = 50 \mu A$, $I_{E} = 0$ | 45 - | 45 - | 45 - | 45 - | 45 - | 45 - | 45 - | 45 - | 45 - | 45 - | |
| | BV _{CEO} | $I_C = 1mA$, $I_B = 0$ | | 45 - | | 45 - | | 45 - | | 45 - | | 45 - | |
| | BV _{EBO} | $I_E = 100 \mu A$, $I_C = 0$ | 1 - | 4 - | 1 - | 4 - | 1 - | 4 - | 1 - | 4 - | 1 - | 4 - | |
| | ^I CB0 | $V_{CB} = 30V, I_{E} = 0$ | - 2 | - 0.5 | - 2 | - 0.5 | - 2 | - 0.5 | - 2 | - 0.5 | - 2 | - 0.5 | μ |
| | СВО | $V_{CB} = 5V$, $I_{E} = 0$, $T = 150^{\circ}C$ | - 50 | - 10 | - 50 | - 10 | - 50 | - 10 | - 50 | - 10 | - 50 | - 10 | μ |
| | СВО | $V_{CB}=30V$, $I_{E}=0$, $T=150^{\circ}C$ | | - 20 | | - 20 | | - 20 | | - 20 | | - 20 | μ |
| | h _{fe} | $I_C = 1\mu A$, $V_{CB} = 5V$, $f = 1kc$ | 9 - 22 | 9 - 22 | 18 - 40 | 18 - 40 | 18 - 90 | 18 - 90 | 36 - 90 | 36 - 90 | 76-333 | 76 - 333 | |
| | h _{ib} | $I_C = 1\mu A$, $V_{CB} = 5V$, $f = 1kc$ | 30 - 80 | 30 - 80 | 30 - 80 | 30 - 80 | 30 - 80 | 30 - 80 | 30 - 80 | 30 - 80 | 30- 80 | 30 - 80 | ! |
| | h _{ob} | $I_C = 1\mu A$, $V_{CB} = 5V$, $f = 1kc$ | - 1.2 | - 1.2 | - 1.2 | - 1.2 | - 1.2 | - 1.2 | - 1.2 | - 1.2 | - 1.2 | - 1.2 | Ω mh |
| | h _{rb} | $I_C = 1\mu A$, $V_{CB} = 5V$, $f = 1kc$ | - 5 | - 5 | - 10 | - 10 | - 10 | - 10 | - 10 | - 10 | - 10 | - 10 | x10 |
| | f∝b | $I_C = 1mA$, $V_{CB} = 5V$ | 1 - | 2.5 - | 2 - | 2.5 - | 8 - | 8 - | 2 - | 2.5 - | 2 - | 2.5 - | m |
| | c_{ob} | $V_{CB} = 5V$, $I_E = 1mA$ | - 30 | - 15 | - 30 | - 15 | - 30 | - 15 | - 30 | - 15 | - 30 | - 15 | t |
| | V _{CE(sat)} | $I_C = 5mA$, $I_B = 2.2mA$ | | - 1 | | - 1 | | - 1 | | - 1 | - `- | - 1 | |
| | R _{cs} | $I_C = 5mA$, $I_B = 1mA$ | - 200 | | - 200 | | - 200 | | - 200 | | - 200 | | ! |
| - 1 | | | | | 1 | ŧ | 1 | l . | 1 | | I | | l . |



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